

MOTIS: A Magneto-Optical Trap-Based Cold Ion Source

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NGT National Institute of Standards and Technology • U.S. Department of Commerce

How can FIBs be improved?

Focused ion beams: an indispensable tool for:

nanofabrication, milling, imaging, surface analysis, etc

Fundamental FIB characteristics:



More makes everything more efficient – picoamps sufficient for many applications



Smaller allows more precision – <10 nm good, <1nm desirable



Wide choice allows new processes – **heavy** for milling, light for imaging, reactive for beam chemistry, specific for doping



Wide choice allows more control – *high* for efficient milling, *low* for reduced sample damage, milling depth control, backscatter analysis



The longer the better – some milling and imaging can be *slow*

The trick: balance tradeoffs, get as much as possible!

How to keep a small focal spot?

1. Keep aberrations, Coulomb interactions under control

2. Keep source emittance small

 $\mathcal{E} = (\langle x \rangle^2 \langle x' \rangle^2 - \langle x x' \rangle^2)^{1/2} \sqrt{U} \longrightarrow$ Volume in transverse phase space: *conserved!*

GOOD



NOTE:

Reducing angular spread also works:

Advantages:

- Completely equivalent to small source
- Moves virtual source far away
- Demagnification becomes very large
 Less sensitive to vibrations
- Current density is smaller (fewer Coulomb interactions)

Not many ways to do this with ions!

Magneto-Optical Trap Ion Source



• Ionize with another laser and extract with a uniform electric field

Ultracold temperature of MOT

- \rightarrow Small transverse velocities
- \rightarrow Low divergence
- \rightarrow Emittance = $\sigma (kT/2)^{1/2}$

• Choice of 22+ ions



- Low energy spread
 - Inherent spread ~neV
 - $^{\rm o}$ Practical spread: geometry-dependent, \propto E

Long term stability

No finicky tip
Macroscopic quantities of ion beam material

MOTIS Source Geometry



- "W" trapping beam configuration
- Another retroreflected beam \perp page
- Top window with ITO conductive coating
- Trapped atoms are ionized and extracted through hole in bottom mirror



Realization: Lithium MOTIS

Why lithium?

- Light ion, low sputtering, good for microscopy
- Interaction with sample should be very different from gallium or helium
- Compact, convenient lasers for cooling



Laser cooling @ 671 nm Ionization @ 350 nm

How much useful current?



- Axial mode high current
- Up to 60 pA observed
- Insert 20 µm aperture in beam
- Measure fraction of current that gets through vs *I*_{tot} and *V*



- Current fraction depends on:
 ➢ Extraction field
 ➢ Total summert
 - ➤ Total current
- Can eliminate effects with more E field

→ MOTIS is a well-characterized, calculable source

Li ion microscope



Lithium ion microscope

- Mount MOTIS on commercial FIB column, supplied through collaboration with FEI Co.
- Laser cooling lasers and optics in rack, coupled by fibers
- Ionization laser is doubled Ti:sapphire, coupled by fiber (not shown)
- Beam scanning, image acquisition handled by FIB system





Lithium MOTIS Images



Sample: broken microchannelplate

Lithium MOTIS Images

Comparison between SEM and Li MOTIS Sample: Si with unknown contamination



SEM: 1 kV, 10 nA



Li MOTIS: 2 kV 10 pA

Beam measurements

2 keV, 1 pA beam



Beam width vs MOT temperature



Lithium MOTIS Images

Best resolution to date: 27 nm at 2 kV





Sample: tin balls on carbon

Sample: graphite

Applications

Li ion beam lithography

With D. Winston, K. Berggren, MIT

- HSQ on Si
- New species could improve resolution, clarify nuclear vs electronic stopping

Li implantation in Si nanowires

With S. Wagesreither, A. Lugstein, TU Wein

• Investigate local diffusion of Li

Li implantation in WO₃

With D. Ruzmetov, A. Talin, CNST

- Modify optical properties on the nanoscale
- Observe Li migration under electric field







Outlook

MOTIS has a "bright" future...

- Construct high voltage Li system
- Bring present source to diffusion limit and beyond?
- Consider other species, e.g. Cs, Er, etc.
- Explore wide range of applications
 - Li implantation
 - Ion lithography
 - Surface modification/damage by Li FIB
 - Secondary yield of Li ion beam from a range of materials
 - Beam chemistry
 - Biological samples
 - Imaging of complex oxides
 - High quality polishing of ion milled surfaces for TEM prep
 - Backscattered ion energy analysis
 - Implantation lithography
 - etc...

AND consider options for even brigher sources (see poster)



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